

Confirmation No. 6969

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	LIU <i>et al.</i>	Examiner:	Unassigned
Serial No.:	10/590,223	Group Art Unit:	2812
Filed:	August 21, 2006	Docket No.:	STFD.071US (S03-201US)

Title: CRYSTALLINE-TYPE DEVICE AND APPROACH THEREFOR

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT (37 C.F.R. §1.97(b))**

MAIL STOP AMENDMENT  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Customer No. <b>40581</b>
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Dear Sir:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner.

This statement should be considered because it is submitted before the mailing date of a first Office Action on the merits for the above-identified application. Accordingly, no fee is due for consideration of the item(s) listed on the enclosed Form 1449.

However, should it be deemed required, authorization is given to charge/credit **Deposit Account 50-0996** (STFD.071US) all required fees/overages to enter this paper.

In accordance with 37 C.F.R. §1.98(a)(2), and the 05 August 2003 Official Gazette Notice, only a copy of each foreign document or non-U.S. patent/application listed on the enclosed Form 1449 would be provided.

Please note that any notations or markings on any attached document do not reflect particular relevance, or lack thereof, to the present application, nor were they necessarily made by anyone affiliated with the prosecution of the present application.

No representation is made that a reference is "prior art" within the meaning of 35 U.S.C. §§ 102 and 103 and Applicants reserve the right, pursuant to 37 C.F.R. § 1.131 or otherwise, to establish that the reference(s) are not "prior art." Moreover, Applicants do not represent that a reference has been thoroughly reviewed or that any relevance of any portion of a reference is intended.


Consideration of the items listed is respectfully requested. Pursuant to the provisions of M.P.E.P. 609, it is requested that the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

Respectfully submitted,

Crawford Maunu PLLC  
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Suite 390  
St. Paul, MN 55120  
651/686-6633

By: 

Robert J. Crawford  
Reg. No. 32,122

Date: June , 2007

<b>FORM 1449*</b> <b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</b>  <b>IN AN APPLICATION</b>  (Use several sheets if necessary)	Docket Number: STFD.071US	Application Number: 10/590,223
	Applicant: LIU <i>et al.</i>	
	Filing Date: Aug. 21, 2006	Group Art Unit: 2812

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6,897,471	5/24/2005	SOREF <i>et al.</i>			
	6,946,318	9/20/2005	WADA <i>et al.</i>			

FOREIGN PATENT DOCUMENTS						
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
	WO2005/094254	13/10/2005	WIPO			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
2006	S. Balakumar <i>et al.</i> "Fabrication Aspects of Germanium on Insulator from Sputtered Ge on Si-Substrates." Electrochemical and Solid-State Letters. Vol. 9, No. 5, p. G158-G160 (2006).	
1984	R. Balasubramanian <i>et al.</i> "Fluid Motion in the Czochralski Method of Crystal Growth." PCH/PhysicoChemical Hydrodynamics. Vol. 5, No. 1, 1984, p. 3-18. <u>ABSTRACT ONLY</u>	
2003	Y. Ishikawa <i>et al.</i> "Strain-Induced Band Gap Shrinkage in GE Grown on Si Substrate." Applied Physics Letters. Vol. 82, No. 13, p. 2044-2046 (March 31, 2003).	
2004	O. I. Dosunmu <i>et al.</i> "Resonant Cavity Enhanced Ge Photodetectors for 1550 nm Operation on Reflecting Si Substrates. IEEE Journal of Selected Topics in Quantum Electronics. vo. 10, No. 4, p. 694-701 (July-Aug 2004).	
2005	Y. H. Kuo <i>et al.</i> "Strong quantum-confined Stark effect in germanium quantum-well structures on silicon." Nature. Vo. 437, No. 27, p. 1334-1336 (27 Oct. 2005).	
1996	M. V. Fischetti <i>et al.</i> "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys." Journal of Applied Physics. Vol. 80, No. 4, p. 2234-2252 (15 Aug. 1996).	

EXAMINER	DATE CONSIDERED
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.	